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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Not For New Designs
Core Processor	R8C
Core Size	16-Bit
Speed	20MHz
Connectivity	CANbus, I²C, LINbus, SIO, SSU, UART/USART
Peripherals	POR, Voltage Detect, WDT
Number of I/O	41
Program Memory Size	96KB (96K x 8)
Program Memory Type	FLASH
EEPROM Size	2K x 8
RAM Size	5K x 8
Voltage - Supply (Vcc/Vdd)	2.7V ~ 5.5V
Data Converters	A/D 12x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	48-LQFP
Supplier Device Package	48-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f2123ajfp-u0

1.2 Performance Overview

Table 1.1 outlines the Functions and Specifications for R8C/22 Group and Table 1.2 outlines the Functions and Specifications for R8C/23 Group.

Table 1.1 Functions and Specifications for R8C/22 Group

Item		Specification
CPU	Number of fundamental instructions	89 instructions
	Minimum instruction execution time	50 ns (f(XIN) = 20 MHz, VCC = 3.0 to 5.5 V) 100 ns (f(XIN) = 10 MHz, VCC = 2.7 to 5.5 V)
	Operating mode	Single-chip
	Address space	1 Mbyte
	Memory capacity	Refer to **Table 1.3 Product Information for R8C/22 Group**
Peripheral Function	Ports	I/O ports: 41 pins, Input port: 3 pins
	Timers	Timer RA: 8 bits x 1 channel, Timer RB: 8 bits x 1 channel (Each timer equipped with 8-bit prescaler) Timer RD: 16 bits x 2 channel (Circuits of input capture and output compare) Timer RE: With compare match function
	Serial interface	1 channel (UART0) Clock synchronous I/O, UART 1 channel (UART1) UART
	Clock synchronous serial interface	1 channel I2C bus interface(2), Clock synchronous serial I/O with chip select
	LIN module	Hardware LIN: 1 channel (timer RA, UART0)
	CAN module	1 channel with 2.0B specification: 16 slots
	A/D converter	10-bit A/D converter: 1 circuit, 12 channels
	Watchdog timer	15 bits x 1 channel (with prescaler) Reset start selectable
	Interrupt	Internal: 14 sources, External: 6 sources, Software: 4 sources, Priority level: 7 levels
	Clock generation circuits	2 circuits XIN clock generation circuit (with on-chip feedback resistor) On-chip oscillator (high speed, low speed) High-speed on-chip oscillator has frequency adjustment function.
	Oscillation stop detection function	Stop detection of XIN clock oscillation
	Voltage detection circuit	On-chip
	Power-on reset circuit include	On-chip
Electric Characteristics	Supply voltage	VCC = 3.0 to 5.5 V (f(XIN) = 20 MHz)(D, J version) VCC = 3.0 to 5.5 V (f(XIN) = 16 MHz)(K version) VCC = 2.7 to 5.5 V (f(XIN) = 10 MHz)
	Current consumption	Typ. 12.5 mA (VCC = 5 V, f(XIN) = 20 MHz, High-speed on-chip oscillator stopping) Typ. 6.0 mA (VCC = 5 V, f(XIN) = 10 MHz, High-speed on-chip oscillator stopping)
Flash Memory	Programming and erasure voltage	VCC = 2.7 to 5.5 V
	Programming and erasure endurance	100 times
Operating Ambient Temperature		-40 to 85°C
		-40 to 125°C (option(1))
Package		48-pin mold-plastic LQFP

NOTES:
1. When using options, be sure to inquire about the specification.
2. I2C bus is a registered trademark of Koninklijke Philips Electronics N.V.

1.3 Block Diagram

Figure 1.1 shows a Block Diagram.

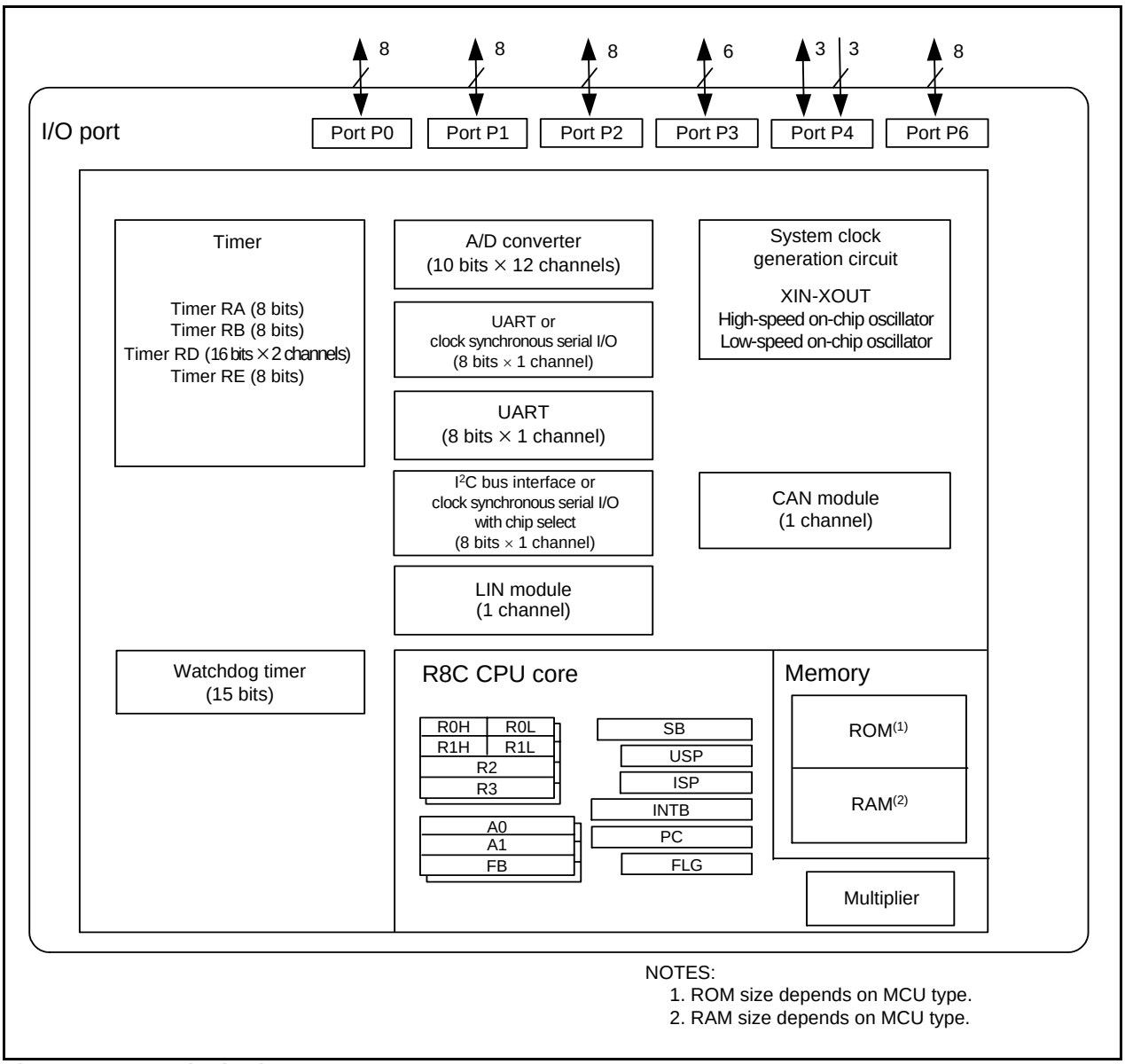


Figure 1.1 Block Diagram

1.4 Product Information

Table 1.3 lists Product Information for R8C/22 Group and Table 1.4 lists Product Information for R8C/23 Group.

Table 1.3 Product Information for R8C/22 Group **Current of Aug. 2008**

Type No.	ROM Capacity	RAM Capacity	Package Type	Remarks	
R5F21226DFP	32 Kbytes	2 Kbytes	PLQP0048KB-A	D version	Flash memory version
R5F21227DFP	48 Kbytes	2.5 Kbytes	PLQP0048KB-A		
R5F21228DFP	64 Kbytes	3 Kbytes	PLQP0048KB-A		
R5F21226JFP	32 Kbytes	2 Kbytes	PLQP0048KB-A	J version	
R5F21227JFP	48 Kbytes	2.5 Kbytes	PLQP0048KB-A		
R5F21228JFP	64 Kbytes	3 Kbytes	PLQP0048KB-A		
R5F2122AJFP	96 Kbytes	5 Kbytes	PLQP0048KB-A		
R5F2122CJFP	128 Kbytes(1)	6 Kbytes	PLQP0048KB-A		
R5F21226KFP	32 Kbytes	2 Kbytes	PLQP0048KB-A	K version	
R5F21227KFP	48 Kbytes	2.5 Kbytes	PLQP0048KB-A		
R5F21228KFP	64 Kbytes	3 Kbytes	PLQP0048KB-A		
R5F2122AKFP	96 Kbytes	5 Kbytes	PLQP0048KB-A		
R5F2122CKFP	128 Kbytes(1)	6 Kbytes	PLQP0048KB-A		

NOTE:
1. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **24. Notes on Emulator Debugger** of Hardware Manual.

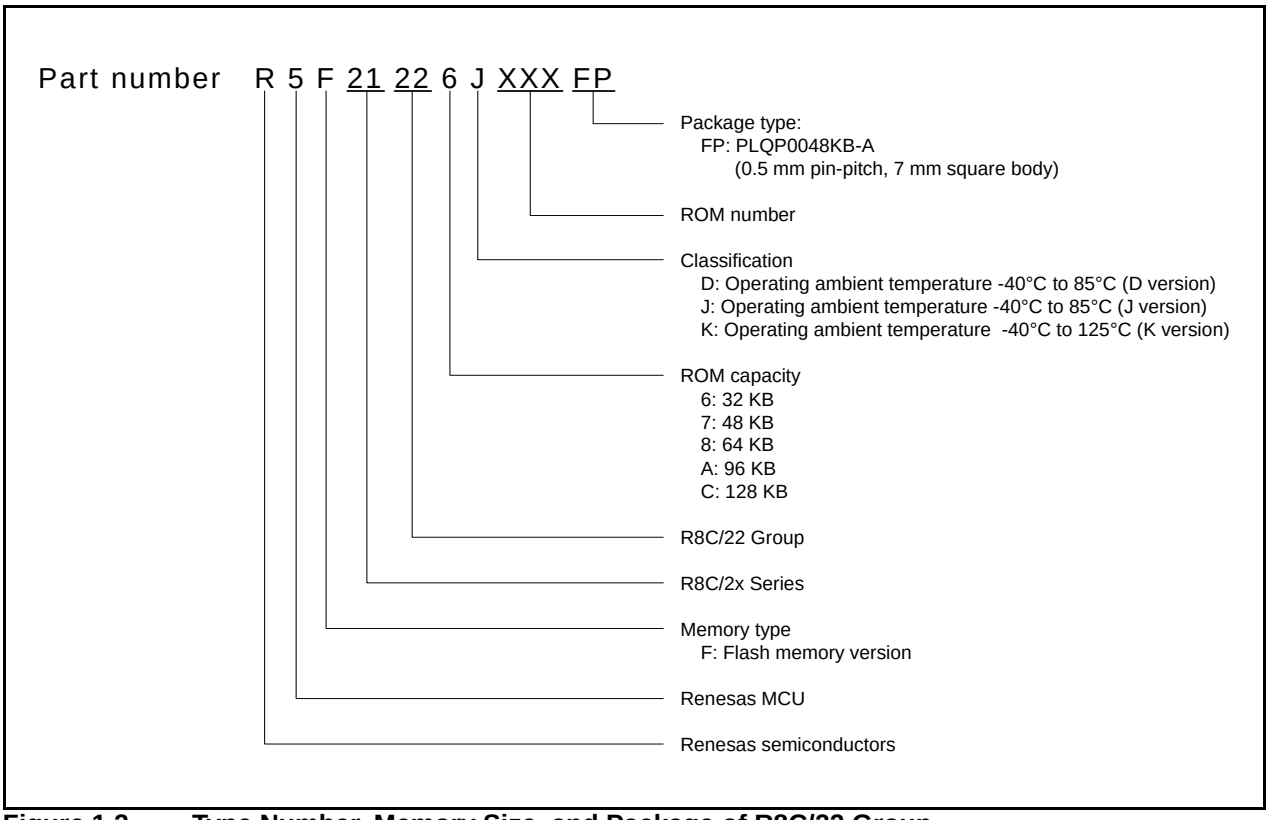


Figure 1.2 Type Number, Memory Size, and Package of R8C/22 Group

Table 1.4 Product Information for R8C/23 Group **Current of Aug. 2008**

Type No.	ROM Capacity		RAM Capacity	Package Type	Remarks	
	Program ROM	Data Flash				
R5F21236DFP	32 Kbytes	1 Kbyte X 2	2 Kbytes	PLQP0048KB-A	D version	Flash memory version
R5F21237DFP	48 Kbytes	1 Kbyte X 2	2.5 Kbytes	PLQP0048KB-A		
R5F21238DFP	64 Kbytes	1 Kbyte X 2	3 Kbytes	PLQP0048KB-A		
R5F21236JFP	32 Kbytes	1 Kbyte X 2	2 Kbytes	PLQP0048KB-A	J version	
R5F21237JFP	48 Kbytes	1 Kbyte X 2	2.5 Kbytes	PLQP0048KB-A		
R5F21238JFP	64 Kbytes	1 Kbyte X 2	3 Kbytes	PLQP0048KB-A		
R5F2123AJFP	96 Kbytes	1 Kbyte X 2	5 Kbytes	PLQP0048KB-A		
R5F2123CJFP	128 Kbytes(1)	1 Kbyte X 2	6 Kbytes	PLQP0048KB-A		
R5F21236KFP	32 Kbytes	1 Kbyte X 2	2 Kbytes	PLQP0048KB-A	K version	
R5F21237KFP	48 Kbytes	1 Kbyte X 2	2.5 Kbytes	PLQP0048KB-A		
R5F21238KFP	64 Kbytes	1 Kbyte X 2	3 Kbytes	PLQP0048KB-A		
R5F2123AKFP	96 Kbytes	1 Kbyte X 2	5 Kbytes	PLQP0048KB-A		
R5F2123CKFP	128 Kbytes(1)	1 Kbyte X 2	6 Kbytes	PLQP0048KB-A		

NOTE:
1. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **24. Notes on Emulator Debugger** of Hardware Manual.

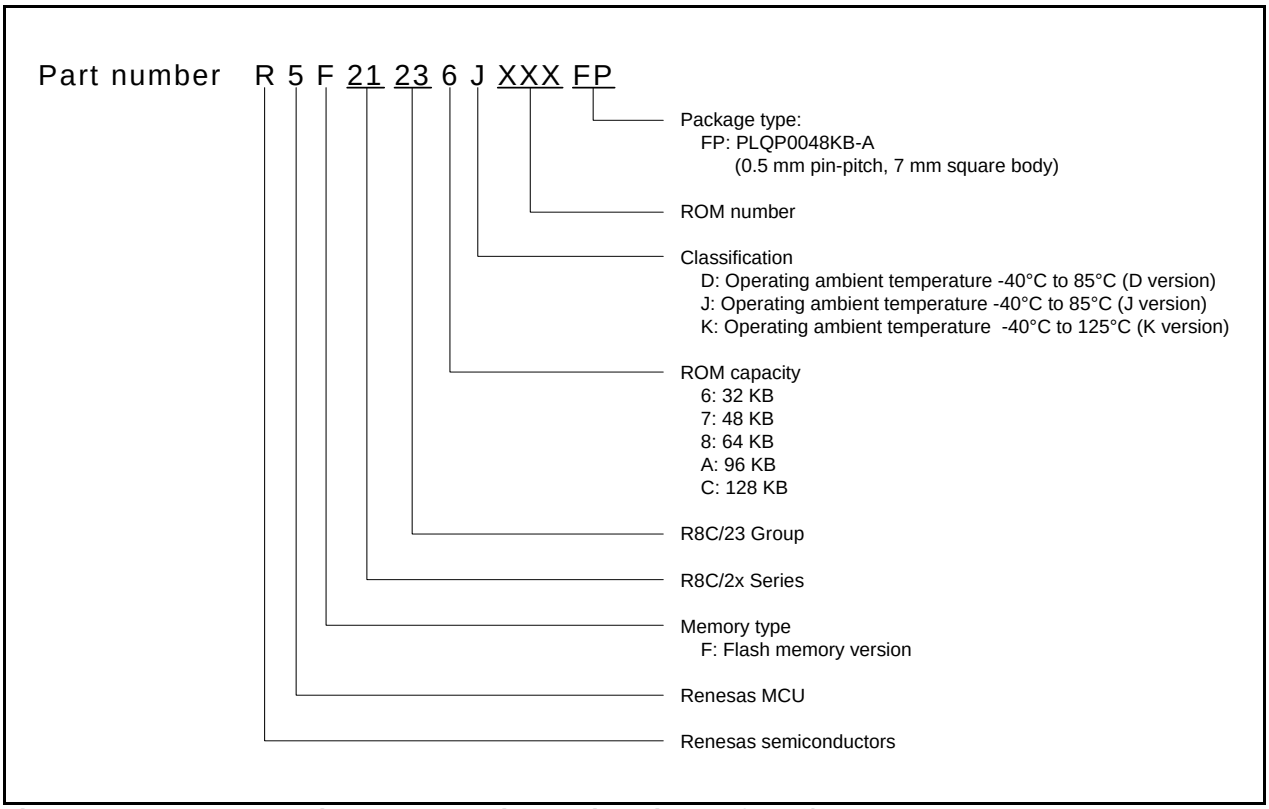
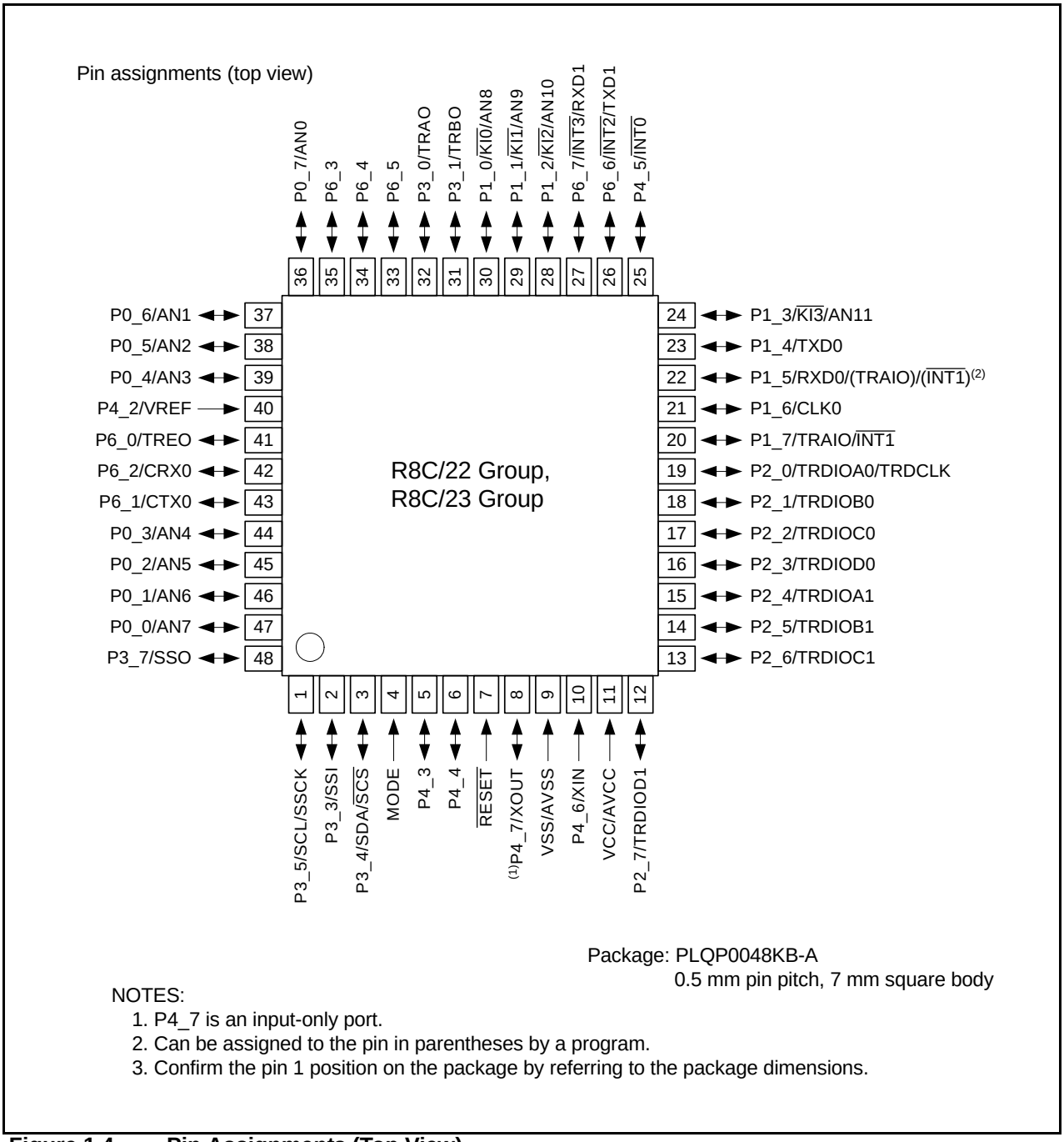


Figure 1.3 Type Number, Memory Size, and Package of R8C/23 Group

1.5 Pin Assignments

Figure 1.4 shows Pin Assignments (Top View).

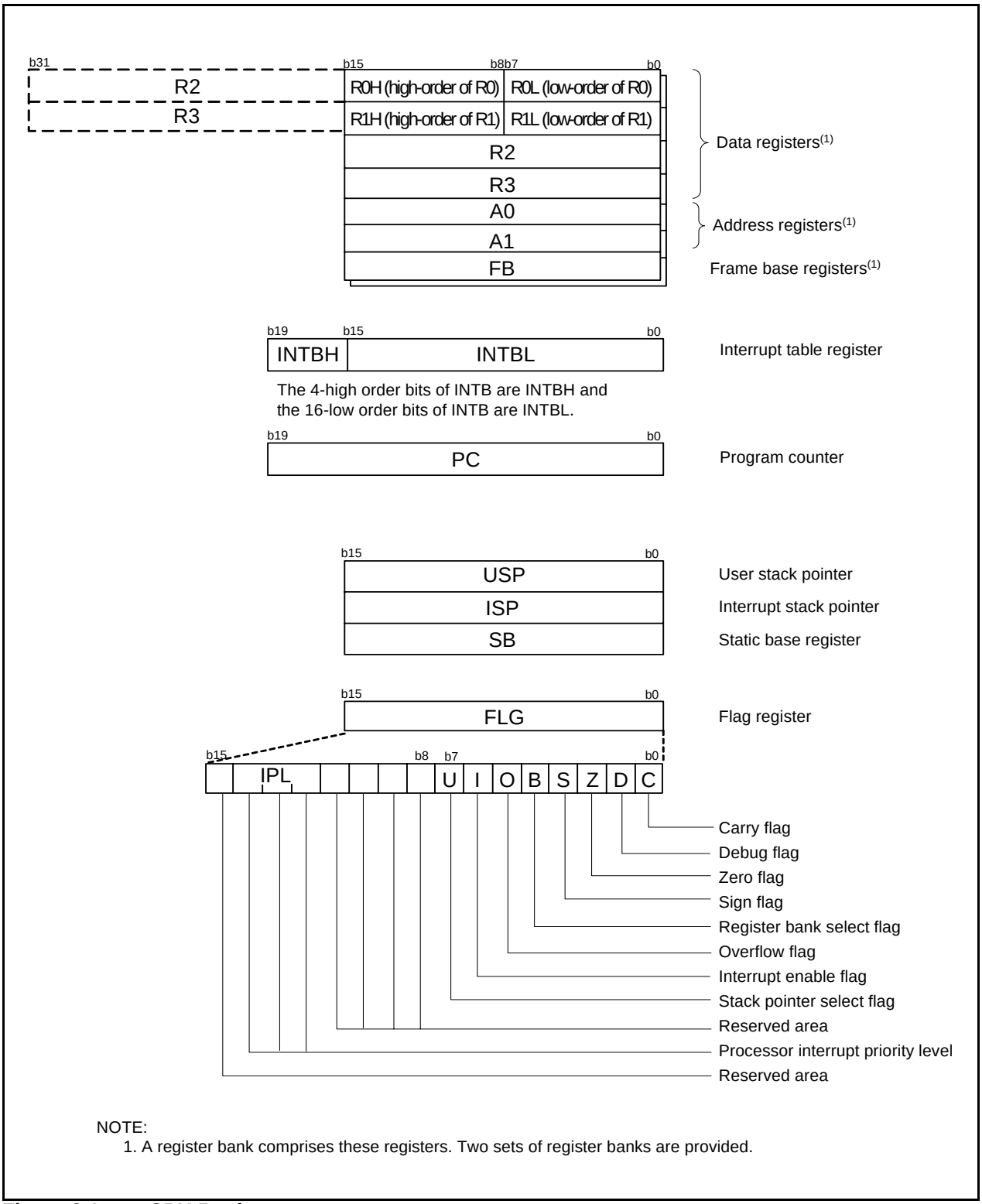


NOTES:
1. P4_7 is an input-only port.
2. Can be assigned to the pin in parentheses by a program.
3. Confirm the pin 1 position on the package by referring to the package dimensions.

Figure 1.4 Pin Assignments (Top View)

2. Central Processing Unit (CPU)

Figure 2.1 shows the CPU Registers. The CPU contains 13 registers. Of these, R0, R1, R2, R3, A0, A1, and FB comprise a register bank. Two sets of register banks are provided.



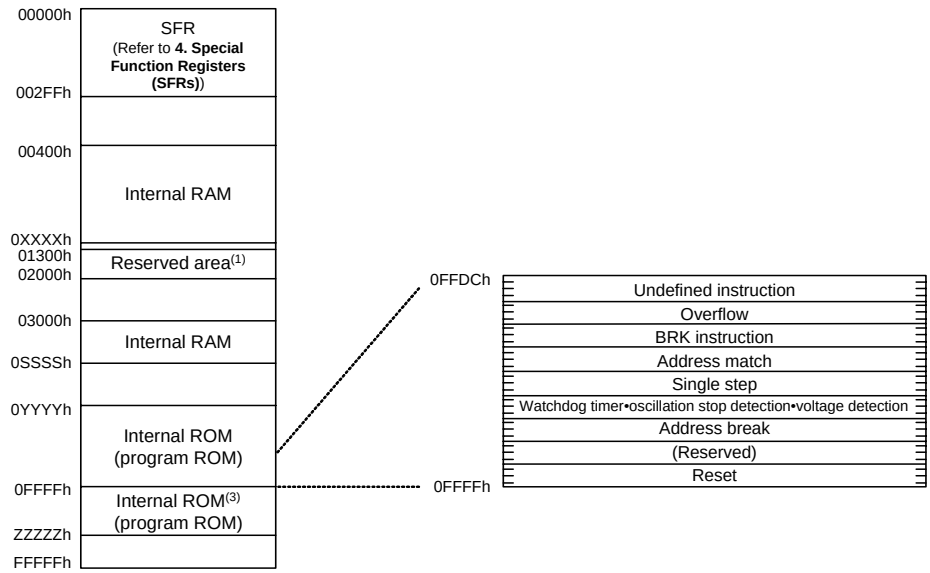
NOTE:
1. A register bank comprises these registers. Two sets of register banks are provided.

Figure 2.1 CPU Registers

3. Memory

3.1 R8C/22 Group

Figure 3.1 shows a Memory Map of R8C/22 Group. The R8C/22 Group has 1 Mbyte of address space from address 00000h to FFFFFh.
The internal ROM is allocated lower addresses, beginning with address 0FFFFh. For example, a 48-Kbyte internal ROM is allocated addresses 04000h to 0FFFFh.
The fixed interrupt vector table is allocated addresses 0FFDCh to 0FFFFh. They store the starting address of each interrupt routine.
The internal RAM is allocated higher addresses, beginning with address 00400h. For example, a 2.5-Kbyte internal RAM is allocated addresses 00400h to 00DFFh. The internal RAM is used not only for storing data but also for calling subroutines and as stacks when interrupt requests are acknowledged.
Special function registers (SFR) are allocated addresses 00000h to 002FFh and 01300h to 0147Fh (SFR area for CAN). The peripheral function control registers are allocated here. All addresses within the SFR, which have nothing allocated are reserved for future user and cannot be accessed by users.



NOTES:
1. SFR area for CAN is allocated addresses 01300h to 0147Fh.
2. The blank regions are reserved. Do not access locations in these regions.
3. Do not use addresses 20000h to 23FFFh because these areas are used for the emulator debugger. Refer to **24. Notes on Emulator Debugger**.

Part Number	Internal ROM			Internal RAM		
	Size	Address 0YYYYh	Address ZZZZZh	Size	Address 0XXXXh	Address 0SSSSh
R5F21226DFP, R5F21226JFP, R5F21226KFP	32 Kbytes	08000h	-	2 Kbytes	00BFFh	-
R5F21227DFP, R5F21227JFP, R5F21227KFP	48 Kbytes	04000h	-	2.5 Kbytes	00DFFh	-
R5F21228DFP, R5F21228JFP, R5F21228KFP	64 Kbytes	04000h	13FFFh	3 Kbytes	00FFFh	-
R5F2122AJFP, R5F2122AKFP	96 Kbytes	04000h	1BFFFh	5 Kbytes	00FFFh	037FFh
R5F2122CJFP, R5F2122CKFP	128 Kbytes	04000h	23FFFh	6 Kbytes	00FFFh	03BFFh

Figure 3.1 Memory Map of R8C/22 Group

Table 4.6 SFR Information (6)(1)

Address	Register	Symbol	After reset
0140h	Timer RD Control Register 0	TRDCR0	00h
0141h	Timer RD I/O Control Register A0	TRDIORA0	10001000b
0142h	Timer RD I/O Control Register C0	TRDIORC0	10001000b
0143h	Timer RD Status Register 0	TRDSR0	11100000b
0144h	Timer RD Interrupt Enable Register 0	TRDIER0	11100000b
0145h	Timer RD PWM Mode Output Level Control Register 0	TRDPOCR0	11111000b
0146h	Timer RD Counter 0	TRD0	00h
0147h			00h
0148h	Timer RD General Register A0	TRDGRA0	FFh
0149h			FFh
014Ah	Timer RD General Register B0	TRDGRB0	FFh
014Bh			FFh
014Ch	Timer RD General Register C0	TRDGRC0	FFh
014Dh			FFh
014Eh	Timer RD General Register D0	TRDGRD0	FFh
014Fh			FFh
0150h	Timer RD Control Register 1	TRDCR1	00h
0151h	Timer RD I/O Control Register A1	TRDIORA1	10001000b
0152h	Timer RD I/O Control Register C1	TRDIORC1	10001000b
0153h	Timer RD Status Register 1	TRDSR1	11000000b
0154h	Timer RD Interrupt Enable Register 1	TRDIER1	11100000b
0155h	Timer RD PWM Mode Output Level Control Register 1	TRDPOCR1	11111000b
0156h	Timer RD Counter 1	TRD1	00h
0157h			00h
0158h	Timer RD General Register A1	TRDGRA1	FFh
0159h			FFh
015Ah	Timer RD General Register B1	TRDGRB1	FFh
015Bh			FFh
015Ch	Timer RD General Register C1	TRDGRC1	FFh
015Dh			FFh
015Eh	Timer RD General Register D1	TRDGRD1	FFh
015Fh			FFh
0160h			
0161h			
0162h			
0163h			
0164h			
0165h			
0166h			
0167h			
0168h			
0169h			
016Ah			
016Bh			
016Ch			
016Dh			
016Eh			
016Fh			
0170h			
0171h			
0172h			
0173h			
0174h			
0175h			
0176h			
0177h			
0178h			
0179h			
017Ah			
017Bh			
017Ch			
017Dh			
017Eh			
017Fh			

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.9 SFR Information (9)(1)

Address	Register	Symbol	After reset
1340h			
1341h			
1342h	CAN0 Acceptance Filter Support Register	C0AFS	XXh
1343h			XXh
1344h			
1345h			
1346h			
1347h			
1348h			
1349h			
134Ah			
134Bh			
134Ch			
134Dh			
134Eh			
134Fh			
1350h			
1351h			
1352h			
1353h			
1354h			
1355h			
1356h			
1357h			
1358h			
1359h			
135Ah			
135Bh			
135Ch			
135Dh			
135Eh			
135Fh	CAN0 Clock Select Register	CCLKR	00h
1360h	CAN0 Slot 0: Identifier/DLC		XXh
1361h			XXh
1362h			XXh
1363h			XXh
1364h			XXh
1365h			XXh
1366h	CAN0 Slot 0: Data Field		XXh
1367h			XXh
1368h			XXh
1369h			XXh
136Ah			XXh
136Bh			XXh
136Ch			XXh
136Dh			XXh
136Eh	CAN0 Slot 0: Time Stamp		XXh
136Fh			XXh
1370h	CAN0 Slot 1: Identifier/DLC		XXh
1371h			XXh
1372h			XXh
1373h			XXh
1374h			XXh
1375h			XXh
1376h	CAN0 Slot 1: Data Field		XXh
1377h			XXh
1378h			XXh
1379h			XXh
137Ah			XXh
137Bh			XXh
137Ch			XXh
137Dh			XXh
137Eh	CAN0 Slot 1: Time Stamp		XXh
137Fh			XXh

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.10 SFR Information (10)(1)

Address	Register	Symbol	After reset
1380h	CAN0 Slot 2: Identifier/DLC		XXh
1381h			XXh
1382h			XXh
1383h			XXh
1384h			XXh
1385h			XXh
1386h	CAN0 Slot 2: Data Field		XXh
1387h			XXh
1388h			XXh
1389h			XXh
138Ah			XXh
138Bh			XXh
138Ch			XXh
138Dh			XXh
138Eh	CAN0 Slot 2: Time Stamp		XXh
138Fh			XXh
1390h	CAN0 Slot 3: Identifier/DLC		XXh
1391h			XXh
1392h			XXh
1393h			XXh
1394h			XXh
1395h			XXh
1396h	CAN0 Slot 3: Data Field		XXh
1397h			XXh
1398h			XXh
1399h			XXh
139Ah			XXh
139Bh			XXh
139Ch			XXh
139Dh			XXh
139Eh	CAN0 Slot 3: Time Stamp		XXh
139Fh			XXh
13A0h	CAN0 Slot 4: Identifier/DLC		XXh
13A1h			XXh
13A2h			XXh
13A3h			XXh
13A4h			XXh
13A5h			XXh
13A6h	CAN0 Slot 4: Data Field		XXh
13A7h			XXh
13A8h			XXh
13A9h			XXh
13AAh			XXh
13ABh			XXh
13ACh			XXh
13ADh			XXh
13AEh	CAN0 Slot 4: Time Stamp		XXh
13AFh			XXh
13B0h	CAN0 Slot 5: Identifier/DLC		XXh
13B1h			XXh
13B2h			XXh
13B3h			XXh
13B4h			XXh
13B5h			XXh
13B6h	CAN0 Slot 5: Data Field		XXh
13B7h			XXh
13B8h			XXh
13B9h			XXh
13BAh			XXh
13BBh			XXh
13BCh			XXh
13BDh			XXh
13BEh	CAN0 Slot 5: Time Stamp		XXh
13BFh			XXh

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 4.11 SFR Information (11)(1)

Address	Register	Symbol	After reset
13C0h	CAN0 Slot 6: Identifier/DLC		XXh
13C1h			XXh
13C2h			XXh
13C3h			XXh
13C4h			XXh
13C5h			XXh
13C6h	CAN0 Slot 6: Data Field		XXh
13C7h			XXh
13C8h			XXh
13C9h			XXh
13CAh			XXh
13CBh			XXh
13CCh			XXh
13CDh			XXh
13CEh	CAN0 Slot 6: Time Stamp		XXh
13CFh			XXh
13D0h	CAN0 Slot 7: Identifier/DLC		XXh
13D1h			XXh
13D2h			XXh
13D3h			XXh
13D4h			XXh
13D5h			XXh
13D6h	CAN0 Slot 7: Data Field		XXh
13D7h			XXh
13D8h			XXh
13D9h			XXh
13DAh			XXh
13DBh			XXh
13DCh			XXh
13DDh			XXh
13DEh	CAN0 Slot 7: Time Stamp		XXh
13DFh			XXh
13E0h	CAN0 Slot 8: Identifier/DLC		XXh
13E1h			XXh
13E2h			XXh
13E3h			XXh
13E4h			XXh
13E5h			XXh
13E6h	CAN0 Slot 8: Data Field		XXh
13E7h			XXh
13E8h			XXh
13E9h			XXh
13EAh			XXh
13EBh			XXh
13ECh			XXh
13EDh			XXh
13EEh	CAN0 Slot 8: Time Stamp		XXh
13EFh			XXh
13F0h	CAN0 Slot 9: Identifier/DLC		XXh
13F1h			XXh
13F2h			XXh
13F3h			XXh
13F4h			XXh
13F5h			XXh
13F6h	CAN0 Slot 9: Data Field		XXh
13F7h			XXh
13F8h			XXh
13F9h			XXh
13FAh			XXh
13FBh			XXh
13FCh			XXh
13FDh			XXh
13FEh	CAN0 Slot 9: Time Stamp		XXh
13FFh			XXh

X: Undefined

NOTE:

1. The blank regions are reserved. Do not access locations in these regions.

Table 5.4 Flash Memory (Program ROM) Electrical Characteristics

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)	R8C/22 Group	100(3)	–	–	times
		R8C/23 Group	1,000(3)	–	–	times
–	Byte program time		–	50	400	µs
–	Block erase time		–	0.4	9	s
$t_{d(SR-SUS)}$	Time delay from suspend request until erase suspend		–	–	97 + CPU clock × 6 cycle	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		0	–	60	°C
–	Data hold time(7)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 100 or 1,000), each block can be erased n times.
   For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Endurance to guarantee all electrical characteristics after program and erase (1 to Min. value can be guaranteed).
4. In a system that executes multiple programming operations, the actual erasure endurance can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
5. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
6. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
7. The data hold time includes time that the power supply is off or the clock is not supplied.

Table 5.5 Flash Memory (Data Flash Block A, Block B) Electrical Characteristics(4)

Symbol	Parameter	Conditions	Standard			Unit
			Min.	Typ.	Max.	
–	Program/erase endurance(2)		10,000(3)	–	–	times
–	Byte program time (Program/erase endurance ≤ 1,000 times)		–	50	400	µs
–	Byte program time (Program/erase endurance > 1,000 times)		–	65	–	µs
–	Block erase time (Program/erase endurance ≤ 1,000 times)		–	0.2	9	s
–	Block erase time (Program/erase endurance > 1,000 times)		–	0.3	–	s
$t_{d(SR-SUS)}$	Time delay from suspend request until erase suspend		–	–	97 + CPU clock × 6 cycle	µs
–	Interval from erase start/restart until following suspend request		650	–	–	µs
–	Interval from program start/restart until following suspend request		0	–	–	ns
–	Time from suspend until program/erase restart		–	–	3 + CPU clock × 4 cycle	µs
–	Program, erase voltage		2.7	–	5.5	V
–	Read voltage		2.7	–	5.5	V
–	Program, erase temperature		-40	–	85(8)	°C
–	Data hold time(9)	Ambient temperature = 55°C	20	–	–	year

NOTES:
1. V_{CC} = 2.7 to 5.5 V at Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), unless otherwise specified.
2. Definition of programming/erasure endurance
   The programming and erasure endurance is defined on a per-block basis.
   If the programming and erasure endurance is n (n = 10,000), each block can be erased n times.
   For example, if 1,024 1-byte writes are performed to different addresses in block A, a 1 Kbyte block, and then the block is erased, the programming/erasure endurance still stands at one. However, the same address must not be programmed more than once per erase operation (overwriting prohibited).
3. Minimum endurance to guarantee all electrical characteristics after program and erase (1 to Min. value can be guaranteed).
4. Standard of block A and block B when program and erase endurance exceeds 1,000 times. Byte program time to 1,000 times are the same as that in program ROM.
5. In a system that executes multiple programming operations, the actual erasure endurance can be reduced by writing to sequential addresses in turn so that as much of the block as possible is used up before performing an erase operation. For example, when programming groups of 16 bytes, the effective number of rewrites can be minimized by programming up to 128 groups before erasing them all in one operation. In addition, averaging the erasure endurance between blocks A and B can further reduce the actual erasure endurance. It is also advisable to retain data on the erasure endurance of each block and limit the number of erase operations to a certain number.
6. If error occurs during block erase, attempt to execute the clear status register command, then the block erase command at least three times until the erase error does not occur.
7. Customers desiring program/erase failure rate information should contact their Renesas technical support representative.
8. 125°C for K version.
9. The data hold time includes time that the power supply is off or the clock is not supplied.

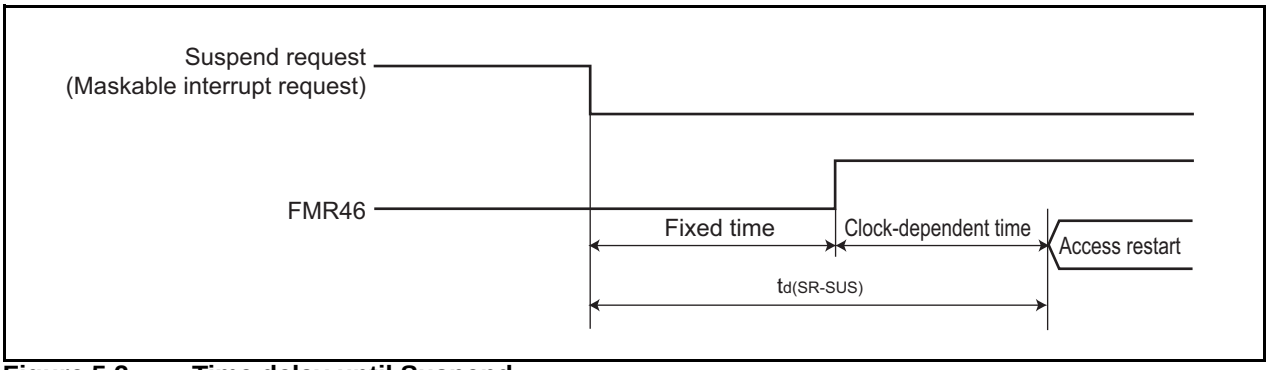


Figure 5.2 Time delay until Suspend

Table 5.6 Voltage Detection 1 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det1}	Voltage detection level(3, 4)		2.70	2.85	3.00	V
$t_{d(Vdet1-A)}$	Voltage monitor 1 reset generation time(5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA26 = 1, V_{CC} = 5.0 V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(2)		–	–	100	µs
Vccmin	MCU operating voltage minimum value		2.70	–	–	V

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and Topr = -40°C to 85°C (D, J version) / -40°C to 125°C (K version).
2. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA26 bit in the VCA2 register to 0.
3. Hold $V_{det2} > V_{det1}$.
4. This parameter shows the voltage detection level when the power supply drops. The voltage detection level when the power supply rises is higher than the voltage detection level when the power supply drops by approximately 0.1 V.
5. Time until the voltage monitor 1 reset is generated after the voltage passes V_{det1} when V_{CC} falls. When using the digital filter, its sampling time is added to $t_{d(Vdet1-A)}$. When using the voltage monitor 1 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det1} when the power supply falls.

Table 5.7 Voltage Detection 2 Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
V_{det2}	Voltage detection level(4)		3.3	3.6	3.9	V
$t_{d(Vdet2-A)}$	Voltage monitor 2 reset/interrupt request generation time(2, 5)		–	40	200	µs
–	Voltage detection circuit self power consumption	VCA27 = 1, V_{CC} = 5.0V	–	0.6	–	µA
$t_{d(E-A)}$	Waiting time until voltage detection circuit operation starts(3)		–	–	100	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 V to 5.5 V and Topr = -40°C to 85°C (D, J version) / -40°C to 125°C (K version).
2. Time until the voltage monitor 2 reset/interrupt request is generated since the voltage passes V_{det2}.
3. Necessary time until the voltage detection circuit operates when setting to 1 again after setting the VCA27 bit in the VCA2 register to 0.
4. Hold $V_{det2} > V_{det1}$.
5. When using the digital filter, its sampling time is added to $t_{d(Vdet2-A)}$. When using the voltage monitor 2 reset, maintain this time until V_{CC} = 2.0 V after the voltage passes V_{det2} when the power supply falls.

Table 5.9 High-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO40M	High-speed on-chip oscillator frequency temperature • supply voltage dependence	V_{CC} = 4.75 V to 5.25 V, 0°C ≤ Topr ≤ 60°C(2)	39.2	40	40.8	MHz
		V_{CC} = 3.0 V to 5.25 V, -20°C ≤ Topr ≤ 85°C(2)	38.8	40	41.2	MHz
		V_{CC} = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 85°C(2)	38.4	40	41.6	MHz
		V_{CC} = 3.0 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	38.0	40	42.0	MHz
		V_{CC} = 2.7 V to 5.5 V, -40°C ≤ Topr ≤ 125°C(2)	37.6	40	42.4	MHz
–	The value of the FRA1 register when the reset is deasserted		08h	40	F7h	–
–	High-speed on-chip oscillator adjustment range	Adjust the FRA1 register to -1 bit (the value when the reset is deasserted)	–	+ 0.3	–	MHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when high-speed on-chip oscillator oscillating	V_{CC} = 5.0 V, Topr = 25°C	–	600	–	µA

NOTES:
1. V_{CC} = 2.7 V to 5.5 V, Topr = -40°C to 85°C (D, J version) / -40°C to 125°C (K version), unless otherwise specified.
2. The standard value shows when the reset is deasserted for the FRA1 register.

Table 5.10 Low-Speed On-Chip Oscillator Circuit Electrical Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
fOCO-S	Low-speed on-chip oscillator frequency		40	125	250	kHz
–	Oscillation stability time		–	10	100	µs
–	Self power consumption when low-speed on-chip oscillator oscillating	V_{CC} = 5.0 V, Topr = 25°C	–	15	–	µA

NOTE:
1. V_{CC} = 2.7 V to 5.5 V, Topr = -40°C to 85°C (D, J version) / -40°C to 125°C (K version), unless otherwise specified.

Table 5.11 Power Supply Circuit Timing Characteristics

Symbol	Parameter	Condition	Standard			Unit
			Min.	Typ.	Max.	
$t_{d(P-R)}$	Time for internal power supply stabilization during power-on(2)		1	–	2000	µs
$t_{d(R-S)}$	STOP exit time(3)		–	–	150	µs

NOTES:
1. The measurement condition is V_{CC} = 2.7 to 5.5 V and Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), unless otherwise specified.
2. Waiting time until the internal power supply generation circuit stabilizes during power-on.
3. Time until CPU clock supply starts since the interrupt is acknowledged to exit stop mode.

Timing Requirements (Unless Otherwise Specified: Vcc = 5 V, Vss = 0 V at Topr = 25°C) [Vcc = 5 V]

Table 5.16 XIN Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(XIN)}$	XIN input cycle time	50	–	ns
$t_{WH(XIN)}$	XIN input “H” width	25	–	ns
$t_{WL(XIN)}$	XIN input “L” width	25	–	ns

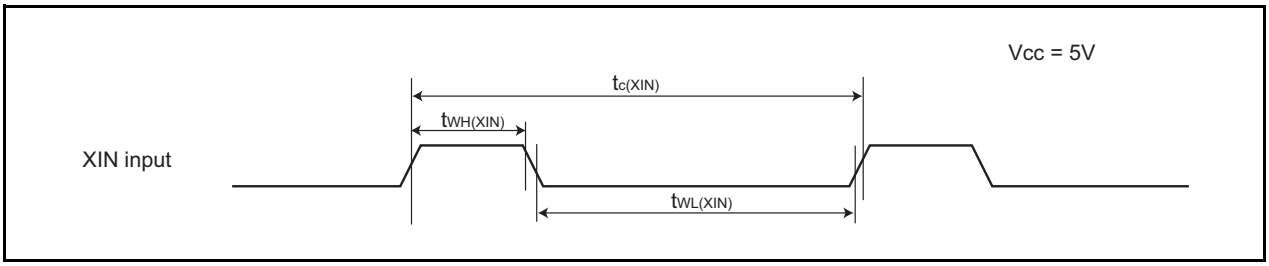


Figure 5.8 XIN Input Timing Diagram when Vcc = 5 V

Table 5.17 TRAIO Input

Symbol	Parameter	Standard		Unit
		Min.	Max.	
$t_{c(TRAIO)}$	TRAIO input cycle time	100	–	ns
$t_{WH(TRAIO)}$	TRAIO input “H” width	40	–	ns
$t_{WL(TRAIO)}$	TRAIO input “L” width	40	–	ns

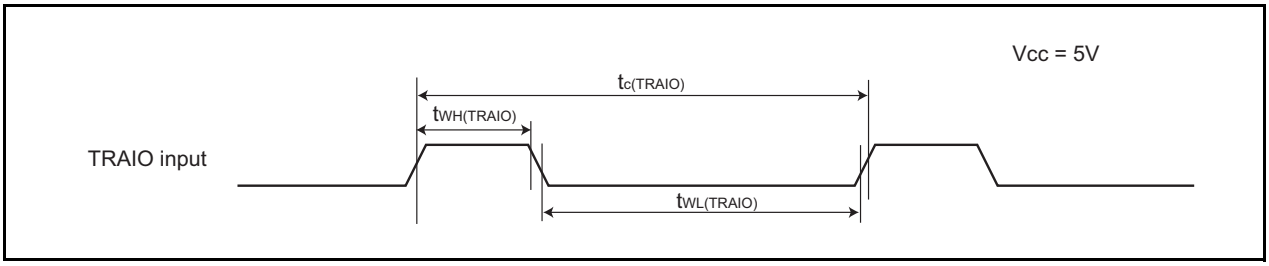


Figure 5.9 TRAIO Input Timing Diagram when Vcc = 5 V

Table 5.20 Electrical Characteristics (3) [Vcc = 3 V]

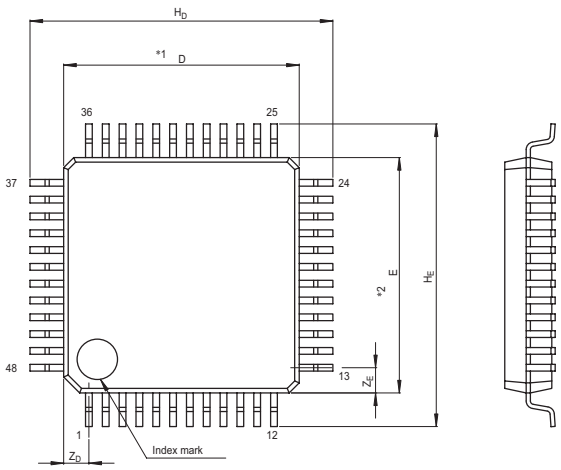
Symbol	Parameter		Condition		Standard			Unit
					Min.	Typ.	Max.	
V_{OH}	Output “H” voltage	Except XOUT	I_{OH} = -1 mA		V_{CC} – 0.5	–	V_{CC}	V
		XOUT	Drive capacity HIGH	I_{OH} = -0.1 mA	V_{CC} – 0.5	–	V_{CC}	V
			Drive capacity LOW	I_{OH} = -50 μA	V_{CC} – 0.5	–	V_{CC}	V
V_{OL}	Output “L” voltage	Except XOUT	I_{OL} = 1 mA		–	–	0.5	V
		XOUT	Drive capacity HIGH	I_{OL} = 0.1 mA	–	–	0.5	V
			Drive capacity LOW	I_{OL} = 50 μA	–	–	0.5	V
V_{T+}-V_{T-}	Hysteresis	$\overline{INT0}$, $\overline{INT1}$, $\overline{INT2}$, $\overline{INT3}$, $\overline{KI0}$, $\overline{KI1}$, $\overline{KI2}$, $\overline{KI3}$, TRAIO, RXD0, RXD1, CLK0, SSI, SCL, SDA, SSO			0.1	0.3	–	V
		$\overline{RESET}$			0.1	0.4	–	V
I_{IH}	Input “H” current		VI = 3 V, Vcc = 3 V		–	–	4.0	μA
I_{IL}	Input “L” current		VI = 0 V, Vcc = 3 V		–	–	-4.0	μA
R_{PULLUP}	Pull-up resistance		VI = 0 V, Vcc = 3 V		66	160	500	kΩ
R_{fXIN}	Feedback resistance	XIN			–	3.0	–	MΩ
V_{RAM}	RAM hold voltage		During stop mode		2.0	–	–	V

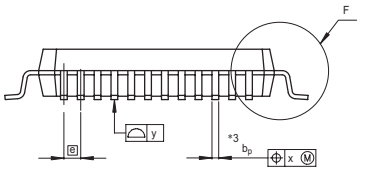
NOTE:
1. V_{CC} = 2.7 to 3.3 V at Topr = -40 to 85°C (D, J version) / -40 to 125°C (K version), f(XIN) = 10 MHz, unless otherwise specified.

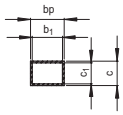
Package Dimensions

Diagrams showing the latest package dimensions and mounting information are available in the “Packages” section of the Renesas Technology website.

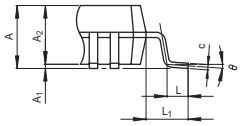
JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
P-LQFP48-7x7-0.50	PLQP0048KB-A	48P6Q-A	0.2g







Terminal cross section



Detail F

NOTE)
1. DIMENSIONS "*1" AND "*2" DO NOT INCLUDE MOLD FLASH.
2. DIMENSION "*3" DOES NOT INCLUDE TRIM OFFSET.

Reference Symbol	Dimension in Millimeters		
	Min	Nom	Max
D	6.9	7.0	7.1
E	6.9	7.0	7.1
A_2	—	1.4	—
H_D	8.8	9.0	9.2
H_E	8.8	9.0	9.2
A	—	—	1.7
A_1	0	0.1	0.2
b_p	0.17	0.22	0.27
b_1	—	0.20	—
c	0.09	0.145	0.20
c_1	—	0.125	—
θ	0°	—	8°
e	—	0.5	—
x	—	—	0.08
y	—	—	0.10
Z_D	—	0.75	—
Z_E	—	0.75	—
L	0.35	0.5	0.65
L_1	—	1.0	—

REVISION HISTORY	R8C/22 Group, R8C/23 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.10	Mar 08, 2005	–	First Edition issued
0.20	Sep 29, 2005	–	Words standardized - Clock synchronous serial interface → Clock synchronous serial I/O - Chip-select clock synchronous interface(SSU) → Clock synchronous serial I/O with chip select - I^2C bus interface(IIC) → I^2C bus interface
		2, 3	Table1.1 R8C/22 Group Performance, Table1.2 R8C/23 Group Performance Serial Interface revised: - Clock Synchronous Serial Interface: 1 channel I^2C bus Interface (3), Clock synchronous serial I/O with chip select - Power-On Reset Circuit added - Power Consumption value determined
		5, 6	Table 1.3 Product Information of R8C/22 Group, Table 1.4 Product Information of R8C/23 Group Date revised.
		7	Figure 1.4 Pin Assignment Pin name revised: - P3_5/$\overline{\text{SSC}}$K(/SCL) → P3_5/ SCL/$\overline{\text{SSC}}$K - P3_4/$\overline{\text{SCS}}$(/SDA) → P3_4/ SDA /$\overline{\text{SCS}}$ - VSS → VSS/AVSS - VCC → VCC/AVCC - P1_5/$\overline{\text{RXD0}}$/(TRAIO/$\overline{\text{INT1}}$) → P1_5/RXD0/(TRAIO)/($\overline{\text{INT1}}$) - P6_6/$\overline{\text{INT2}}$/(TXD1) → P6_6/$\overline{\text{INT2}}$/TXD1 - P6_7/$\overline{\text{INT3}}$/(RXD1) → P6_7/$\overline{\text{INT3}}$/RXD1 - NOTE2 added
		8	Table 1.5 Pin Description - Analog Power Supply Input: line added - I^2C Bus Interface (IIC) → I^2C Bus Interface - SSU → Clock Synchronous Serial I/O with Chip Select
		9	Table 1.6 Pin Name Information by Pin Number revised - Pin Number 1: (SCL) → SCL - Pin Number 2: (SDA) → SDA - Pin Number 9: VSS → VSS/AVSS - Pin Number 11: VCC → VCC/AVCC - Pin Number 26: (TXD1) → TXD1 - Pin Number 27: (RXD1) → RXD1
		15	Table 4.1 SFR Information (1) revised - 0013h: XXXXXX00b → 00h
		17	Table 4.3 SFR Information (3) revised - 00BCh: 0000X000b → 00h/0000X000b
		18	Table 4.4 SFR Information (4) revised - 00D6h: 00000XXXb → 00h - 00F5h: UART1 Function Select Register added
		19	Table 4.5 SFR Information (5) revised - 0104h: TRATR → TRA

REVISION HISTORY	R8C/22 Group, R8C/23 Group Datasheet

Rev.	Date	Description	
		Page	Summary
0.20	Sep 29, 2005	20	Table 4.6 SFR Information (6) revised - 0145h: POCR0 → TRDPOCR0 - 0146h, 0147h: TRDCNT0 → TRD0 - 0148h, 0149h: GRA0 → TRDGRA0 - 014Ah, 014Bh: GRB0 → TRDGRB0 - 014Ch, 014Dh: GRC0 → TRDGRC0 - 014Eh, 014Fh: GRD0 → TRDGRD0 - 0155h: POCR1 -> TRDPOCR1 - 0156h, 0157h: TRDCNT1 → TRD1 - 0158h, 0159h: GRA1 → TRDGRA1 - 015Ah, 015Bh: GRB1 → TRDGRB1 - 015Ch, 015Dh: GRC1 → TRDGRC1 - 015Eh, 015Fh: GRD1 → TRDGRD1
		28	5. Electrical Characteristics added
1.00	Oct 27, 2006	All pages	"Preliminary" and "Under development" deleted
		2	Table 1.1 Functions and Specifications for R8C/22 Group revised. NOTE1 deleted.
		3	Table 1.2 Functions and Specifications for R8C/23 Group revised. NOTE1 deleted.
		5	Table 1.3 Product Information for R8C/22 Group; "R5F2122AJFP (D)", "R5F2122CJFP (D)", "R5F2122AKFP (D)", "R5F2122CKFP (D)", and NOTE added. Figure 1.2 Type Number, Memory Size, and Package of R8C/22 Group; "A: 96 KB" and "C: 128 KB" added.
		6	Table 1.4 Product Information for R8C/23 Group; "R5F2123AJFP (D)", "R5F2123CJFP (D)", "R5F2123AKFP (D)", "R5F2123CKFP (D)", and NOTE added. Figure 1.3 Type Number, Memory Size, and Package of R8C/23 Group; "A: 96 KB" and "C: 128 KB" added.
		13	Figure 3.1 Memory Map of R8C/22 Group revised.
		14	Figure 3.2 Memory Map of R8C/23 Group revised.
		15	Table 4.1 SFR Information (1)(1); NOTE8; "The CSPROINI bit in the OFS register is set to 0." → "The CSPROINI bit in the OFS register is 0." revised.
		28	Table 5.1 Absolute Maximum Ratings; Power dissipation revised. Table 5.2 Recommended Operating Conditions; System clock revised.
		33	Table 5.8 Voltage Monitor 1 Reset Circuit Electrical Characteristics → Table 5.8 Power-on Reset Circuit, Voltage Monitor 1 Reset Circuit Electrical Characteristics(1) replaced. Table 5.8 revised. NOTE3 added. Table 5.9 Power-on Reset Circuit Electrical Characteristics deleted. Figure 5.3 Power-on Reset Circuit Electrical Characteristics revised.
		34	Table 5.10 High-Speed On-Chip Oscillator Circuit Electrical Characteristics → Table 5.9 High-Speed On-Chip Oscillator Circuit Electrical Characteristics revised.